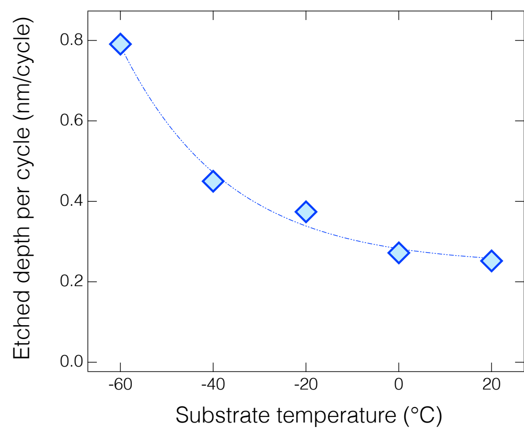

Fig. 1 Dependence of etched depth per cycle (EPC) of the SiO2 ALE on the substrate temperature (T_s).

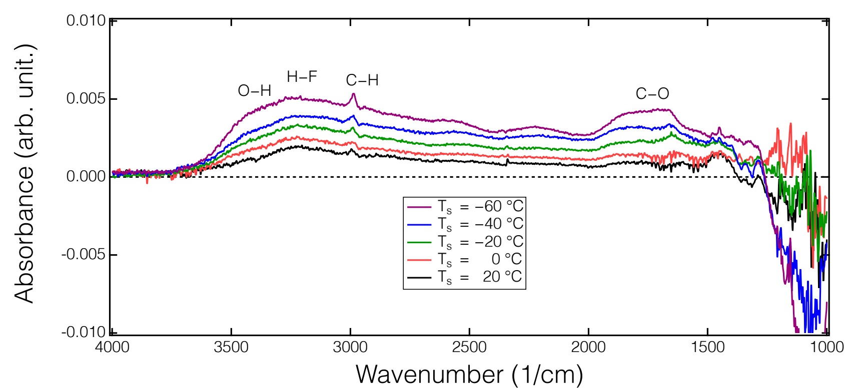

Fig. 2 Absorbance changes of the SiO_2 after introducing HF/C_2H_5OH gases in the each first half-cycle for the Cryo-ALE at different substrate temperatures (T_s).